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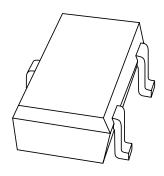
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PMST2369 NPN switching transistor

Product data sheet Supersedes data of 1997 May 05 1999 Apr 22



NPN switching transistor

PMST2369

FEATURES

• Low current (max. 200 mA)

• Low voltage (max. 15 V).

APPLICATIONS

 High-speed switching applications, primarily in portable and consumer equipment.

DESCRIPTION

NPN switching transistor in a SOT323 plastic package.

MARKING

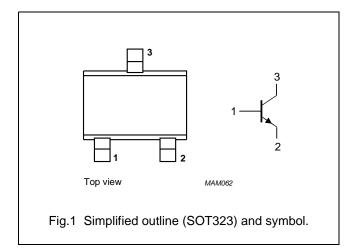
TYPE NUMBER	MARKING CODE ⁽¹⁾		
PMST2369	*1J		

Note

* = - : Made in Hong Kong.
 * = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	-	15	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		-	200	mA
I _{CM}	peak collector current	$t_p \le 10 \mu s$	-	300	mA
I _{BM}	peak base current		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN switching transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

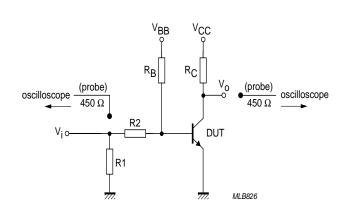
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 20 V	_	400	nA
		I _E = 0; V _{CB} = 20 V; T _j = 125 °C	-	30	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 4 V	_	100	nA
h _{FE}	DC current gain	$I_C = 10 \text{ mA}; V_{CE} = 1 \text{ V}$	40	120	
		$I_C = 10 \text{ mA}; V_{CE} = 1 \text{ V}; T_{amb} = -55 ^{\circ}\text{C}$	20	_	
		I _C = 100 mA; V _{CE} = 2 V; note 1	20	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	_	250	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$	700	850	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 5$ V; $f = 1$ MHz	_	4	pF
f _T	transition frequency	$I_C = 10 \text{ mA}$; $V_{CE} = 10 \text{ V}$; $f = 100 \text{ MHz}$	500	_	MHz
Switching ti	Switching times (between 10% and 90% levels); (see Fig.2)				
t _{on}	turn-on time	I _{Con} = 10 mA; I _{Bon} = 3 mA;	_	10	ns
t _d	delay time	$I_{Boff} = -1.5 \text{ mA}$	_	4	ns
t _r	rise time		_	6	ns
t _{off}	turn-off time		_	20	ns
t _s	storage time		_	10	ns
t _f	fall time		_	10	ns

Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

NPN switching transistor

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 V_i = 0.5 V to 4.2 V; T = 500 $\mu s;$ t_p = 10 $\mu s;$ t_r = $t_f \leq$ 1 ns.

R1 = 56 Ω ; R2 = 1 k Ω ; R_B = 1 k Ω ; R_C = 270 Ω .

 V_{BB} = 0.2 V; V_{CC} = 2.7 V.

Oscilloscope: input impedance $Z_i = 50 \Omega$.

Fig.2 Test circuit for switching times.

1999 Apr 22

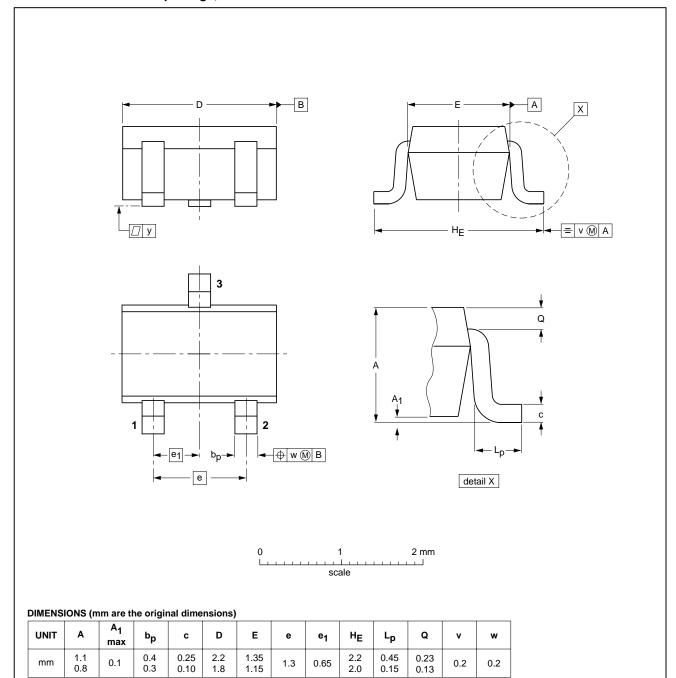
NPN switching transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



OUTLINE		REFERENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT323			SC-70			97-02-28

NPN switching transistor

PMST2369

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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